

isc Silicon PNP Power Transistor

2SB630

DESCRIPTION

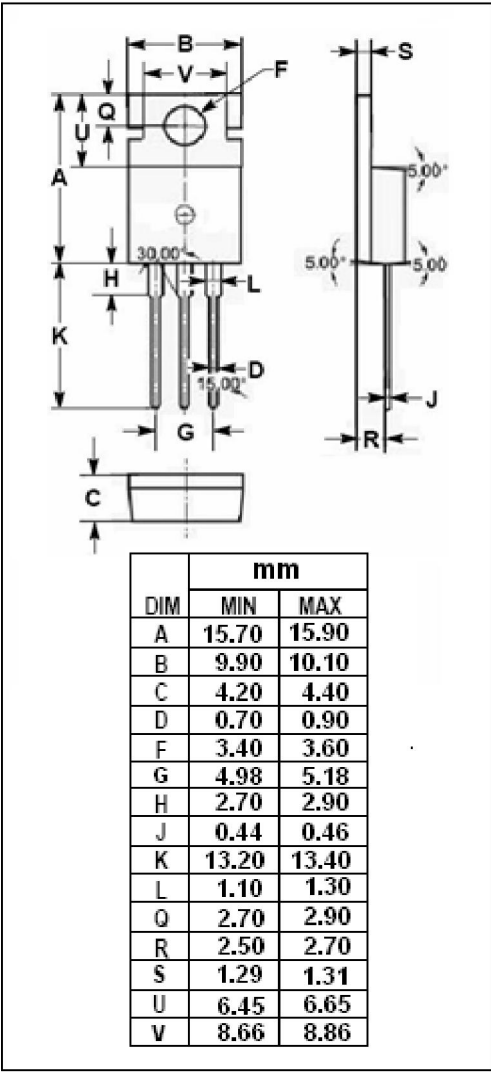
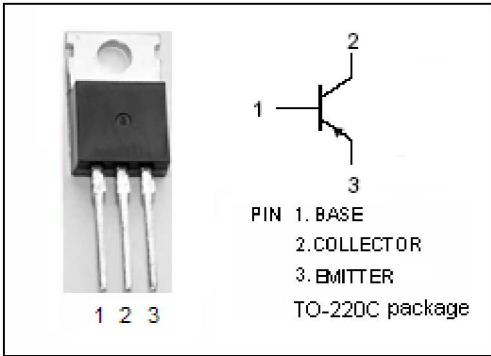
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -200V(\text{Min})$
- Complement to Type 2SD610

APPLICATIONS

- Audio frequency power amplifier applications.
- Suitable for driver of 200~300 watts audio amplifier.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-200	V
V_{CEO}	Collector-Emitter Voltage	-200	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-2	A
I_{CM}	Collector Current-Peak	-3.0	A
P_C	Collector Power Dissipation @ $T_a=25^{\circ}\text{C}$	1.5	W
	Collector Power Dissipation @ $T_c=25^{\circ}\text{C}$	25	
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}\text{C}$



isc Silicon PNP Power Transistor**2SB630****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -0.5A; I _B = -50mA			-1.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = -0.5A; I _B = -50mA			-1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -150V; I _E = 0			-1.0	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -3V; I _C = 0			-1.0	μ A
h _{FE-1}	DC Current Gain	I _C = -5mA; V _{CE} = -10V	20			
h _{FE-2}	DC Current Gain	I _C = -0.5A; V _{CE} = -10V	40		200	
C _{OB}	Collector Output Capacitance	I _E = 0; V _{CB} = -10V; f= 1MHz		65		pF
f _T	Current-Gain—Bandwidth Product	I _C = -0.5A; V _{CE} = -10V		4		MHz

◆ **h_{FE-2} Classifications**

S	R	Q
40-80	60-120	100-200